

RMSB40B THRU RMSB40M

GLASS PASSIVATED SURFACE MOUNT BRIDGE RECTIFIERS

Features

♦ Glass Passivated Chip Junction

◆ Reverse Voltage - 100 to 1000 V

◆ Forward Current- 4.0 A

◆ Fast reverse recovery time

◆ Designed for Surface Mount Application

Mechanical Data

Case : JEDEC UMSB molded plastic body

Terminals: Solderable per MIL-STD-750, Method 2026Á Á

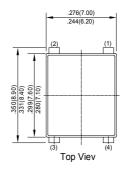
Polarity: Polarity symbol marking on body

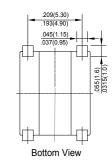
Mounting Position: Any

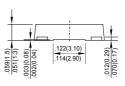
Weight: 0.00825 ounce, 0.234 grams

UMSB











Dimensions in inches and (millimeters)

Maximum Ratings And Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	Symbols	MDD	MDD	MDD	MDD	MDD	MDD	Units
Marking Code		RMSB40B	RMSB40D	RMSB40G	RMSB40J	RMSB40K	RMSB40M	Omto
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current	I _{F(AV)}	4					Α	
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	95					А	
Maximum Forward Voltage at 4.0 A	V _F	1.3					V	
	I _R	5.0 200					μA	
Typical Junction Capacitance (Note 1)	C _j	50					pF	
Typical Thermal Resistance (Note2)	$\begin{array}{c} R_{\theta JA} \\ R_{\theta JC} \\ R_{\theta JL} \end{array}$	60 15 25					°C/W	
Maximum Reverse Recovery Time (Note3)	t _{rr}		150		250	50	00	ns
Operating and Storage Temperature Range	T_j , T_{stg}	-55 ~ +150				°C		

Note: 1. Measured at 1MHz and applied reverse voltage of 4 V D.C.

- 2. Mounted on glass epoxy PC board with4×1.5"×1.5" (3.81×3.81 cm) copper pad areas.
- 3. Measured with I = 0.5 A, I = 1 A, Irr = 0.25 A .





Typical Characterisitics

Fig.1 Average Rectified Output Current Derating Curve

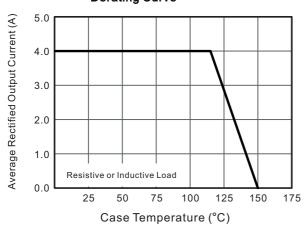


Fig.2 Typical Reverse Characteristics

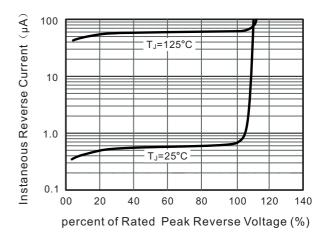


Fig.3 Typical Instaneous Forward Characteristics

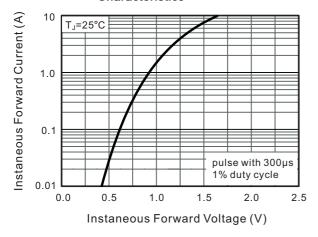


Fig.4 Typical Junction Capacitance

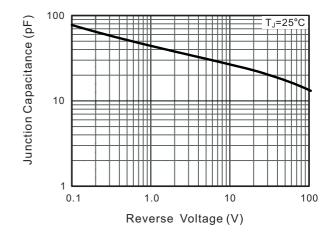


Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

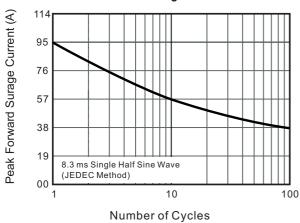
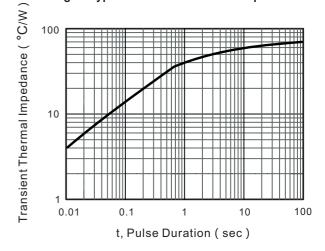


Fig.6- Typical Transient Thermal Impedance



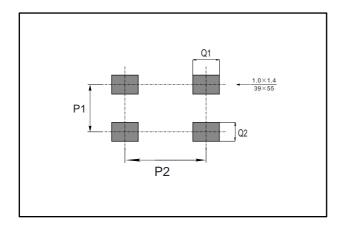
The curve above is for reference only.

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Suggested Pad Layout



Dim	Min
P1	5.1
P2	7.1
Q1	1.8
Q2	1.3

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